

IN THE CLAIMS

Please amend claims 1, 14 and 16 as follows:

Sub
C1
B1
1. (Twice Amended) A solid-state image pickup device, comprising:
a pixel portion having unit pixels arranged two-dimensionally in a matrix form, each of said unit pixels including a photoelectrically transducing element for photoelectrically transducing incident light to obtain a signal charge, and stocking the signal charge thus obtained, a selection switch for selecting one of the pixels, and a read-out switch for reading out the signal charge from said photoelectrically transducing element to one of a plurality of vertical signal lines;

a plurality of amplifying means, at least one of the amplifying means being connected to each of said respective vertical signal lines and for converting the signal charge read out to the vertical signal lines to an electrical signal; and

a plurality of reset means for resetting each of said vertical signal lines;

wherein each of said selection switch and said read-out switch comprises a MOS transistor having a double gate structure, and

wherein each gate electrode of said selection switch and said read-out switch comprises a two-layer gate electrode, and neighboring portions are overlapped with each other.

Sub
C1
B2
Cnd
14. (Twice Amended) A method of driving a solid-state image pickup device comprising a pixel portion having unit pixels arranged two-dimensionally in a matrix form, each of said unit pixels including a photoelectrically transducing element for photoelectrically transducing incident light to obtain a signal charge and stocking the signal charge thus obtained, a selection switch for selecting one of the pixels, and a read-out switch for reading out the signal charge from said photoelectrically transducing element to one of a plurality of vertical signal lines; a plurality of amplifying means at least one of which are connected to each of said respective vertical signal lines and for converting the signal charge read out to the vertical signal lines to an electrical signal, and a plurality of reset means for resetting each of said vertical signal lines, the method comprising the steps of:

resetting the vertical signal line;

after resetting the vertical signal line, reading out a pixel signal from said photoelectrically transducing element to the vertical signal line to successively output a reset level and a signal level in this order through the same route; and

after reading out the pixel signal, calculating a difference between the reset level and the signal level, wherein each of said selection switch and said read-out switch comprises a MOS transistor having a double gate structure,

wherein each gate electrode of said selection switch and said read-out switch comprises a two-layer gate electrode, and neighboring portions are overlapped with each other.

16. (Twice Amended) A camera comprising:
an optical system for focusing incident light from a subject onto a solid-state image pickup device;
a driving system for driving said solid-state image pickup device; and
a signal processing system for processing an output signal of said solid-state image pickup device, wherein said solid-state image pickup device comprises a pixel portion having unit pixels arranged two-dimensionally in a matrix form, each of said unit pixels including a photoelectrically transducing element for photoelectrically transducing incident light to obtain signal charge, and stocking the signal charge thus obtained, a selection switch for selecting one of the pixels, and a read-out switch for reading out the signal charge from said photoelectrically transducing element to one of a plurality of vertical signal lines, a plurality of means, at least one of which are connected to each of said respective vertical signal lines and for converting the signal charge read out to the vertical signal lines to an electrical signal, and a plurality of reset means for resetting each of said vertical signal lines, and wherein said driving system drives said solid-state image pickup device so that one of the vertical signal lines is first reset and then a pixel signal is read out from said photoelectrically transducing element to the vertical signal line to successively output a reset level and a signal level in this order through the same route, and thereafter calculates a difference between the reset level and the signal level, and wherein each of said selection switch and said read-out switch comprises a MOS transistor having a double gate structure, and

wherein each gate electrode of said selection switch and said read-out switch comprises a two-layer gate electrode, and neighboring portions are overlapped with each other.

Please cancel claim 8.